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Transistors Panasonic

2SB0710A

Silicon PNP epitaxial planar type

For general amplification Complementary to 2SD0602A

■ Features

- Large collector current I_C
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_{C}	- 0.5	A	
Peak collector current	I _{CP}	-1	A	
Collector power dissipation	$P_{\rm C}$	200	mW	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

■ Package

• Code

Mini3-G1

- Pin Name
 - 1: Base
 - 2: Emitter
 - 3: Collector
- Marking Symbol: D

■ Electrical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu{\rm A}, I_{\rm E} = 0$	-60	70.		V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -10 \text{ mA}, I_B = 0$	-50	0,		V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\rm CB} = -20 \text{ V}, I_{\rm E} = 0$	19		- 0.1	μΑ
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	85		340	_
	h _{FE2}	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	40			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		-0.35	-0.60	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		-1.1	-1.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		6	15	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

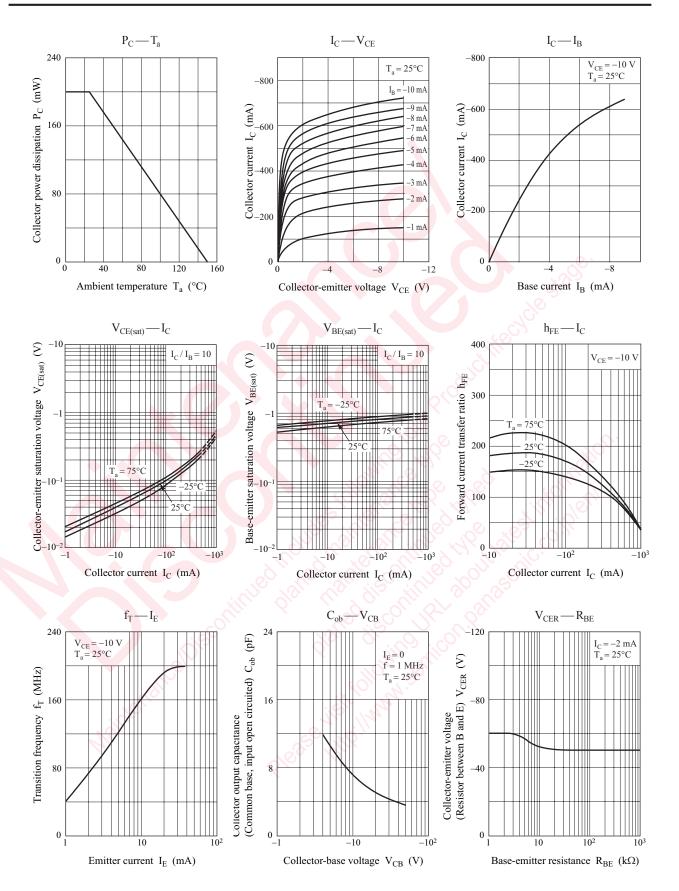
- 2. *1: Pulse measurement
 - *2: Rank classification

Rank	Q	R	S	No-rank
h_{FE1}	85 to 170	120 to 240	170 to 340	85 to 340
Marking symbol	DQ	DR	DS	D

Product of no-rank is not classified and have no indication for rank.

2SB0710A

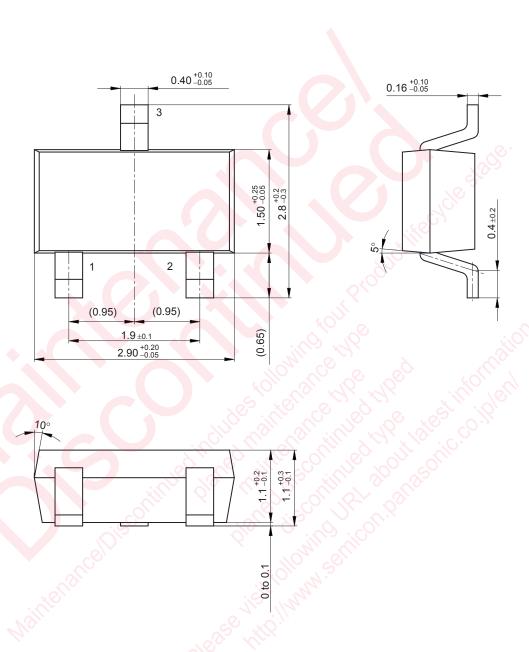
Panasonic



2 SJC00413AED

Panasonic 2SB0710A

Mini3-G1 Unit: mm



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